TECHNICAL DATA DATA SHEET 4324, REV. -

LOW RDS HERMETIC POWER MOSFET - P-CHANNEL

FEATURES:

- 150 Volt, 0.1 Ohm, 7A MOSFET
- Isolated Hermetic Metal Package
- Ultra Low R_{DS (on)}
- Characterized at V_{GS} of 6V

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_c = 25^{\circ}\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
ON-STATE DRAIN CURRENT	I _{D25}	-	-	- 7	Amps
PULSED DRAIN CURRENT	I _{DM}	-	-	- 50	Amps
OPERATING AND STORAGE TEMPERATURE	T _J /T _{STG}	-55	-	+150	°C
TOTAL DEVICE DISSIPATION	P_{D}	-	-	40	Watts
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{\theta JC}$	-	-	3.1	°C/W

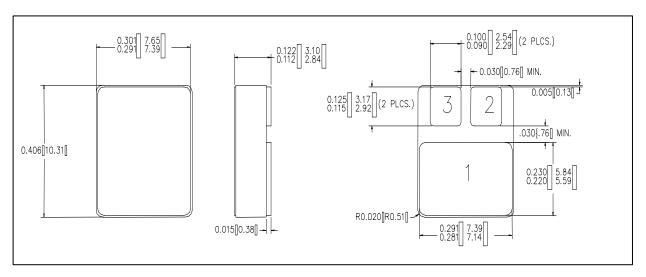
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC		SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE		BV _{DSS}	-150	-	-	Volts
	$V_{GS} = 0V$, $I_D = -250 \mu A$					
STATIC DRAIN TO SOURCE ON STATE RESISTANCE						Ω
	$I_{GS} = -10V, I_{D} = -7A$	-	-	0.09	0.10	
	$I_{GS} = -6V, I_{D} = -5A$		-	0.10	0.11	
GATE THRESHOLD VOLTAGE V	$I_{\rm DS} = V_{\rm GS}, I_{\rm D} = -250 \mu A$	$V_{GS(th)}$	- 2	-	- 4	Volts
FORWARD TRANSCONDUCTANO		9 _{fs}	-	19	-	S(1/Ω)
	$V_{DS} = -15V, I_{D} = -7A$					
ZERO GATE VOLTAGE DRAIN CU						
V _{DS} = 0.8 x Max. rating		I _{DSS}	-	-	- 1	μΑ
	T _J = 125°C				- 50	
GATE TO SOURCE LEAKAGE FO	00	I _{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE RE				_	-100	
TURN ON DELAY TIME	$V_{DD} = -75V$	$t_{d(ON)}$	-	25	40	
RISE TIME	$I_D = -5A$	t _r		46	70	nsec
TURN OFF DELAY TIME	V _{GS} = - 10V			445	400	
EALL TIME		t _{d(OFF)}		115	180	
FALL TIME	$R_G = 6\Omega$	t _f		64	100	
DIODE FORWARD VOLTAGE	$I_F = -5A, V_{GS} = 0V$	V_{SD}	-	0.9	1.2	Volts
	µs, duty cycle d ≤ 2 %					
REVERSE RECOVERY TIME	$T_{J} = 25^{\circ}C,$			400	450	
	$I_F = -3A$, $V_R = 100V$	t _{rr}	-	100	150	nsec
	di/dt = 100A/μsec					
TOTAL GATE CHARGE	$V_{DD} = -75V$	Q_g	-	88	-	
GATE SOURCE CHARGE	$I_D = -5A$	Q_{gs}		18		nC
GATE DRAIN CHARGE	$V_{GS} = -10V$	Q_{gd}		27		

SENSITRON

TECHNICAL DATA DATA SHEET 4234, REV. -

MECHANICAL DIMENSIONS: in Inches / mm



LCC-5

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
P Channel Mosfet	DRAIN	GATE	SOURCE

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